#### HBT small-signal analysis

1

#### LECTURE 16

- Base current
- DC equivalent circuit
- AC small-signal analysis
- Hybrid-π equivalent circuit
- Parasitic R and C in an HBT
- Capacitance in a BT

#### **Base current: components**

#### Base current components in active mode



• Which  $I_B$  components do we need to consider?

Sec. 9.3

#### Base current: recombination in base QNR



# Sec. 9.3 Base current components and Gummel plot



### DC Equivalent circuit



## AC small-signal operation



Notation

Linearize

 $i_J(t) = I_J + i_j(t)$  J, j = 1, 2, 3,

Match the numbers to the terminals

Function of 2 variables

 $i_{2} = I_{2}(V_{21} + v_{21}, V_{31} + v_{31})$   $= I_{2}(V_{21}, V_{31}) + \frac{\partial I_{2}}{\partial V_{21}}v_{21} + \frac{\partial I_{2}}{\partial V_{31}}v_{31}$   $\equiv I_{2} + g_{22}v_{21} + g_{23}v_{31},$ 

Does the linearization set limits for the small signal?

Sec. 14.2

## AC small-signal equivalent circuit



## Hybrid-π equivalent circuit

Sec. 14.3



#### Capacitance

#### Generally:

$$C \equiv \frac{\partial Q}{\partial V}$$

Specifically:

$$C_{jk} = -\frac{\partial Q_j}{\partial V_k} \quad \text{if } j \neq k$$
$$C_{jk} = +\frac{\partial Q_j}{\partial V_k} \quad \text{if } j = k$$



#### Sec. **Emitter-base junction-storage capacitance** 12.3.1 **R** - $\rightarrow$ $\vdash$ $\leftarrow$ W<sub>B2</sub> **QNB** QNE QNC $W_{B1}$ + $\Delta V_{\text{BE}}$





- $\Delta Q_{E,j}$  is the change in charge entering the device through the emitter and creating the new width of the depletion layer (narrowing it in this example),
- $\bullet$  in response to a change in  $V_{\text{BE}}$  (with E & C at AC ground).
- It can be regarded as a parallel-plate cap.

What is the voltage dependence of this cap?





•  $\Delta Q_{E,b}$  is the change in charge entering the device through the emitter and resting in the base (the black electrons),

11

- $\bullet$  in response to a change in  $V_{\text{BE}}$  (with E & C at AC ground).
- It's not a parallel-plate cap, and we only count one carrier.



#### Emitter-base base-storage capacitance: evaluation



$$Q_{E,b}(V_{BE}) = -q \frac{1}{2} W_B A \left[ n_{0p} \exp(\frac{V_{BE}}{V_{th}}) - n(W_B) \right] - q W_B A n(W_B)$$
  
Take  $\frac{\Delta Q_{E,b}}{\Delta V_{BE}} \rightarrow \frac{d Q_{E,b}}{d V_{BE}}$   
Hence  $C_{EB,b}$ 

$$\frac{n(0, V_{BE1}) = n_{0p} \exp(V_{BE1} / V_{th})}{n(0, V_{BE2}) = n_{0p} \exp(V_{BE2} / V_{th})}$$

What is the voltage dependence of  $C_{EB,b}$  ?